# A" tomoti e 750 V, 660 A Single Side Direct Cooling 6-Pack Po er Mod" le

# **VE-Trac™ Direct Mod**<sup>\*</sup> le **NVH660S75L4SPFC**

#### **Product Description**

The NVH660S75L4SPFC is a power module from the VE-Trac™ Direct family of highly integrated power modules with industry standard footprints for Hybrid (HEV) and Electric Vehicle (EV) traction inverter application.

The module integrates six Field Stop 4 (FS4) 750 V Narrow Mesa IGBTs in a 6-pack configuration, which excels in providing high current density, while offering robust short circuit protection and increased blocking voltage. Additionally, FS4 750 V Narrow Mesa IGBTs show low power losses during lighter loads, which helps to improve overall system efficiency in automotive applications.

For assembly ease and reliability, a new generation of press-fit pins

#### **Pin Description**

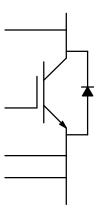


Figure 1. Pin Description

# $\textbf{MODULE CHARACTERISTICS} \ (T_{vj} = 25^{\circ}C, \ \underline{Unless \ Otherwise \ Specified)}$

Symbol	Parameter	Rating	Unit
т т			•

<b>CHARACTERISTICS OF IGBT</b> (T <sub>vj</sub> = 25		

# $\textbf{CHARACTERISTICS OF INVERSE DIODE} \ (T_{vj} = \underbrace{25^{\circ}C}, \ Unless \ Otherwise \ Specified)$

Symbol	Parameters	Conditions		Min	Тур	Max	Unit
V <sub>F</sub>	Diode Forward Voltage (Terminal)	I <sub>F</sub> = 450 A	T <sub>vj</sub> = 25°C	-	1.51	1.76	V
	Diode Forward Voltage (Chip)	I <sub>F</sub> = 450 A	$T_{vj} = 25^{\circ}C$ $T_{vj} = 150^{\circ}C$ $T_{vj} = 175^{\circ}C$	- - -	1.45 1.33 1.30	1.70 - -	
		I <sub>F</sub> = 660 A	$T_{vj} = 25^{\circ}C$ $T_{vj} = 150^{\circ}C$ $T_{vj} = 175^{\circ}C$	- - -	1.58 1.52 1.50	- - -	
E <sub>rr</sub>	Reverse Recovery Energy	$I_F = 450 \text{ A}, V_F = 400 \text{ V}, V_{GE} = +15/-8 \text{ V}, Rg.on = 4 \Omega$	di/dt = 3.5 A/nS, $T_{vj}$ = 25°C di/dt = 3.0 A/nS, $T_{vj}$ = 150°C	-	2 7	-	mJ
			$T_{vj} = 130 \text{ C}$ di/dt = 2.9  A/nS, $T_{vj} = 175 ^{\circ}\text{C}$	-	9	-	
Q <sub>rr</sub>	Recovered Charge	$I_F = 450 \text{ A}, V_F = 400 \text{ V},$ $V_{GE} = -8 \text{ V},$	$di/dt = 3.5 \text{ A/nS},$ $T_{vj} = 25^{\circ}\text{C}$	-	7	-	μС
		Rg.on = $4 \Omega$	di/dt = 3.0  A/nS, $T_{vj} = 150^{\circ}\text{C}$	-	26	-	
			$di/dt = 2.9 \text{ A/nS},$ $T_{vj} = 175^{\circ}\text{C}$	-	33	-	
I <sub>rr</sub>	Peak Reverse Recovery Current	$I_F = 450 \text{ A}, V_F = 400 \text{ V},$ $V_{GE} = -8 \text{ V},$	$di/dt = 3.5 \text{ A/nS},$ $T_{vj} = 25^{\circ}\text{C}$	-	120	-	Α
		Rg.on = $4 \Omega$	di/dt = 3.0  A/nS, $T_{vi} = 150^{\circ}\text{C}$	-	227	-	
			di/dt = 2.9 A/nS, T <sub>vj</sub> = 175°C	-	264	-	

## NTC SENSOR CHARACTERISTICS ( $T_{vj} = 25$ °C, Unless Otherwise Specified)

Symbol	Parameters	Conditions	Min	Тур	Max	Unit
R <sub>25</sub> (Note 3)	Rated Resistance	T <sub>C</sub> = 25°C	-	5147	-	Ω
ΔR/R	Deviation of R105	$T_C = 105^{\circ}C, R_{105} = 472 \Omega$	5	_	5	%
P <sub>25</sub>	Power Dissipation	T <sub>C</sub> = 25°C	-	_	32	mW
B <sub>25/55</sub>	B-Value	$R = R_{25} \exp \left[ B_{25/55} \left( 1/T - 1/298 \right) \right]$	-	3340	-	K
B <sub>25/85</sub>	B-Value	$R = R_{25} \exp \left[ B_{25/85} \left( 1/T - 1/298 \right) \right]$	-	3360	-	K
B <sub>25/105</sub>	B-Value	$R = R_{25} \exp \left[ B_{25/105} \left( 1/T - 1/298 \right) \right]$	-	3364	_	K

<sup>2.</sup> Measured value at terminals.

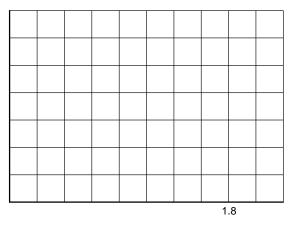
#### THERMAL CHARACTERISTICS

Symbol	Symbol Parameter		Тур	Max	Unit
IGBT.R <sub>th,J-C</sub>	Rth, Junction to Case	-	0.074	0.085	°C/W
IGBT.R <sub>th,J-F</sub> Rth, Junction to Fluid, 10 L/min, 65°C, 50/50 EGW, Ref. Coolinig Jacket		_	0.15		°C/W
Diode.R <sub>th,J-C</sub> Rth, Junction to Case		-	0.13	0.15	°C/W
Diode.R <sub>th,J-F</sub>	Rth, Junction to Fluid, 10 L/min, 65°C, 50/50 EGW, Ref. Coolinig Jacket	-	0.23		°C/W

#### **ORDERING INFORMATION**

Part Number	Package	Shipping
NVH660S75L4SPFC	SSDC33, 154.50x92.0 (SPFC) (Pb-Free)	4 Units / Tray

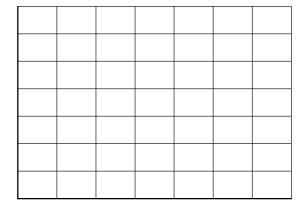
#### **TYPICAL CHARACTERISTICS**

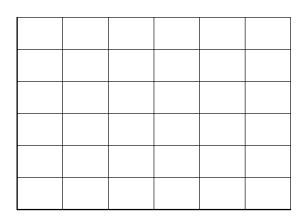


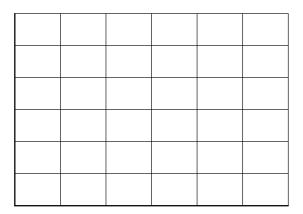
V<sub>CE</sub> (V)

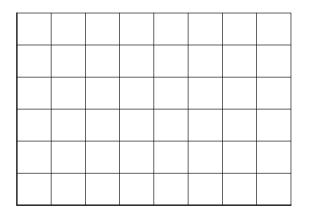
Figure 2. IGBT Output Characteristic



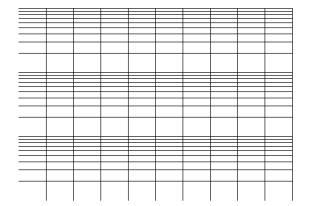


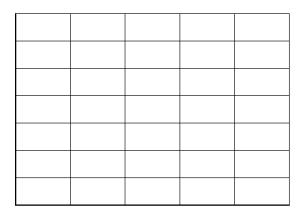




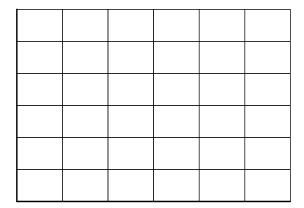


#### **TYPICAL CHARACTERISTICS**





#### **TYPICAL CHARACTERISTICS**



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